

Description

The SX5N10SI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 100V$ $I_D = 5A$

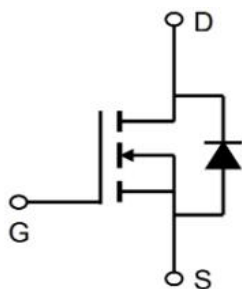
$R_{DS(ON)} < 110m\Omega$ @ $V_{GS}=10V$

Application

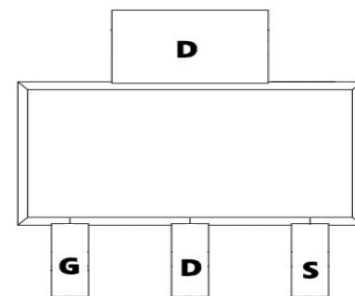
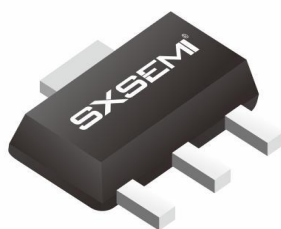
Lithium battery protection

Wireless impact

Mobile phone fast charging



SOT-89-3L



Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	5	A
$I_D @ T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	3.6	A
I_{DM}	Pulsed Drain Current ²	15	A
$P_D @ T_A=25^\circ\text{C}$	Total Power Dissipation ³	3.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	85	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	40	$^\circ\text{C/W}$

Electrical Characteristics (T_c=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	100	---	---	V
ΔBVDSS/ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C , I _D =1mA	---	0.122	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =3A	---	88	110	mΩ
		V _{GS} =4.5V , I _D =2A	---	95	125	mΩ
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.6	2.5	V
ΔVGS(th)	VGS(th) Temperature Coefficient		---	-4.84	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =100V , V _{GS} =0V , T _J =25°C	---	---	10	uA
		V _{DS} =100V , V _{GS} =0V , T _J =55°C	---	---	100	
IGSS	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =2A	---	10.2	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	2.3	4.6	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =60V , V _{GS} =10V , I _D =2A	---	25.5	---	nC
Q _{gs}	Gate-Source Charge		---	4.2	---	
Q _{gd}	Gate-Drain Charge		---	4.3	---	
Td(on)	Turn-On Delay Time	V _{DD} =50V , V _{GS} =10V , R _G =3.3Ω I _D =1A	---	17.3	---	ns
T _r	Rise Time		---	2.8	---	
Td(off)	Turn-Off Delay Time		---	50	---	
T _f	Fall Time		---	2.8	---	
Ciss	Input Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz	---	677	---	pF
Coss	Output Capacitance		---	46	---	
Crss	Reverse Transfer Capacitance		---	32	---	
IS	Continuous Source Current ^{1,4}	V _G =V _D =0V , Force Current	---	---	2	A
ISM	Pulsed Source Current ^{2,4}		---	---	4	A
VSD	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C	---	---	1.2	V

Note :

- 1 、 The data tested by surface mounted on a 1 inch ² FR-4 board with 2OZ copper.
- 2 、 The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3 、 The power dissipation is limited by 150°C junction temperature
- 4 、 The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

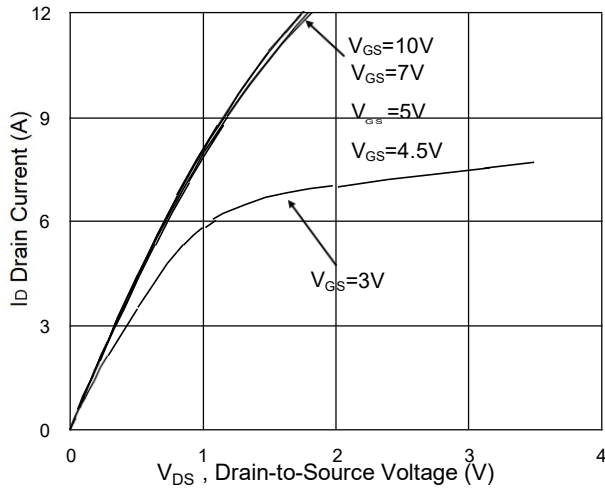


Fig.1 Typical Output Characteristics

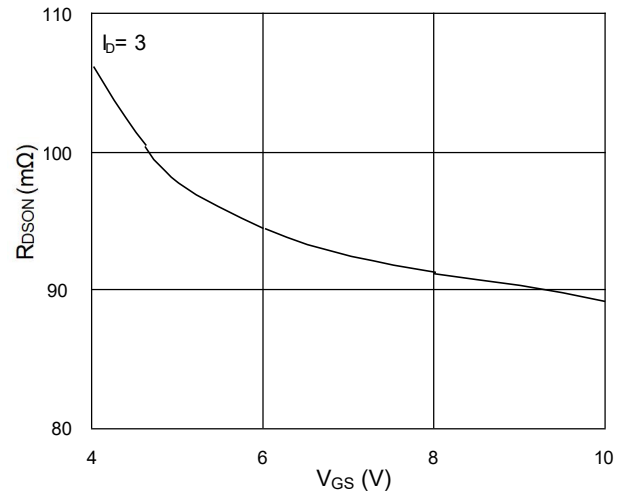


Fig.2 On-Resistance vs. Gate-Source

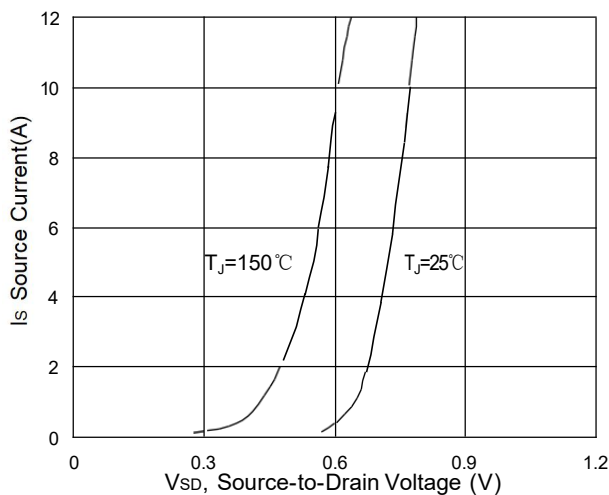


Fig.3 Forward Characteristics Of Reverse

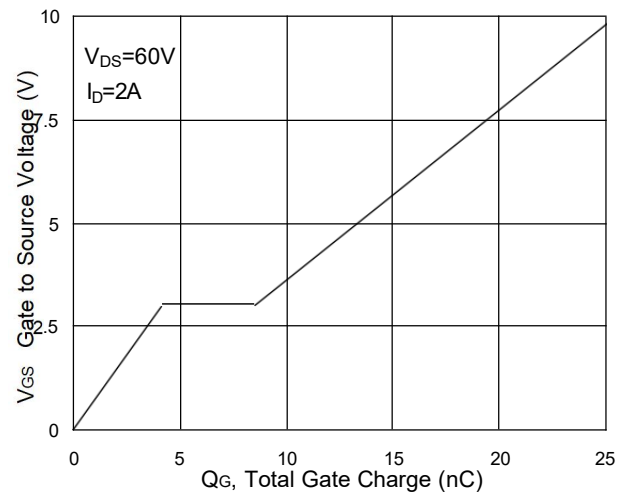


Fig.4 Gate-Charge Characteristics

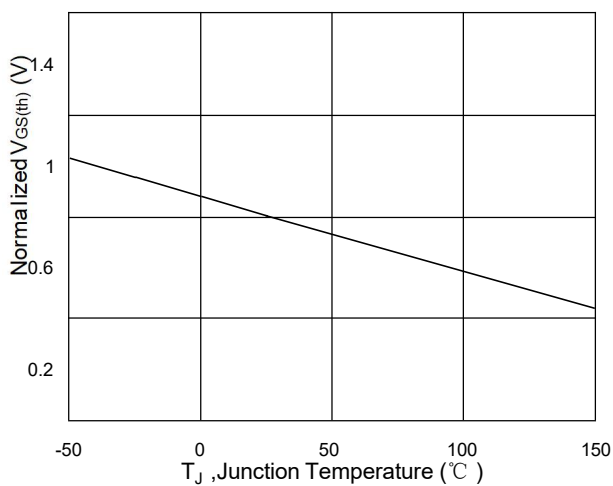


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

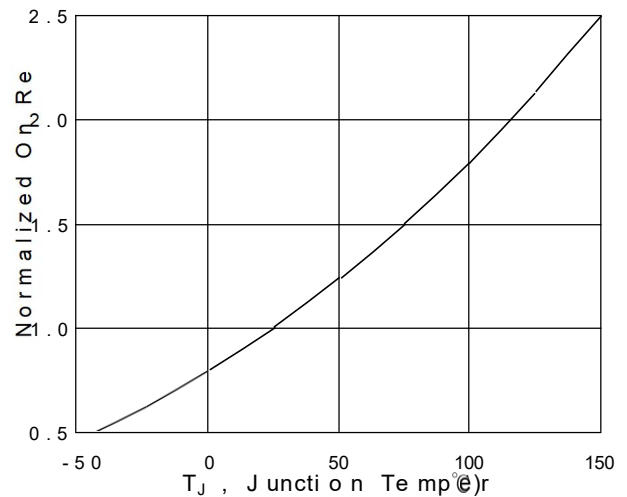


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

Typical Characteristics

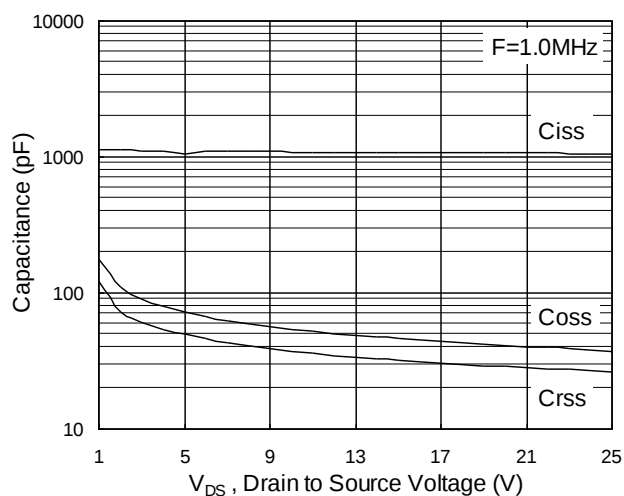


Fig.7 Capacitance

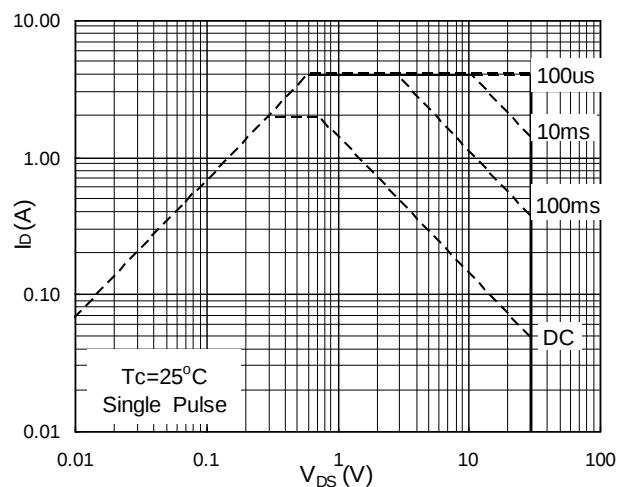


Fig.8 Safe Operating Area

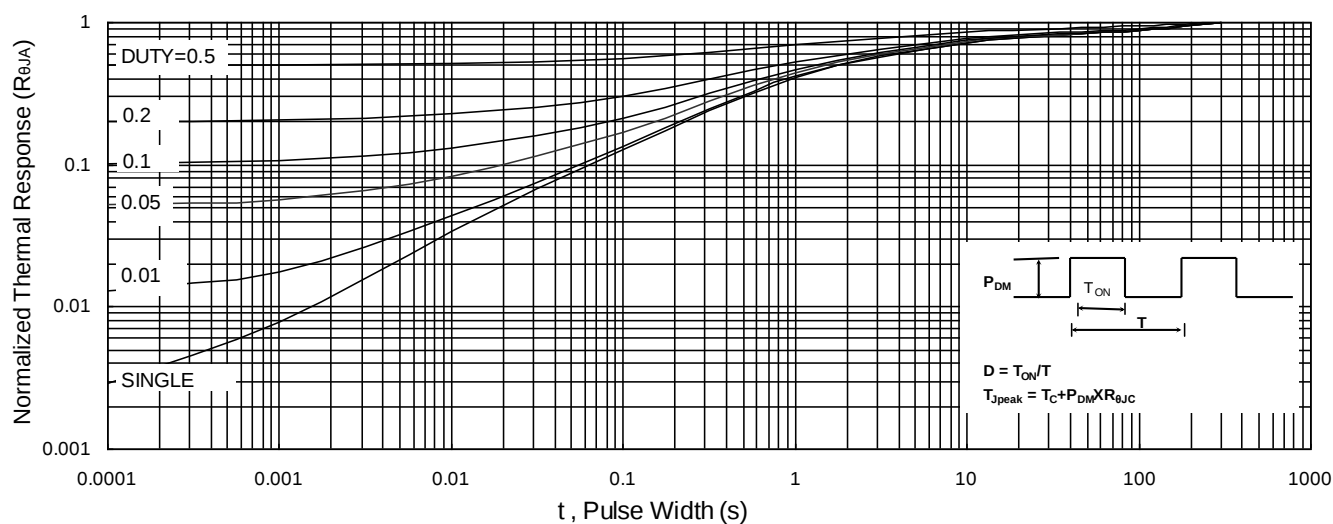


Fig.9 Normalized Maximum Transient Thermal Impedance

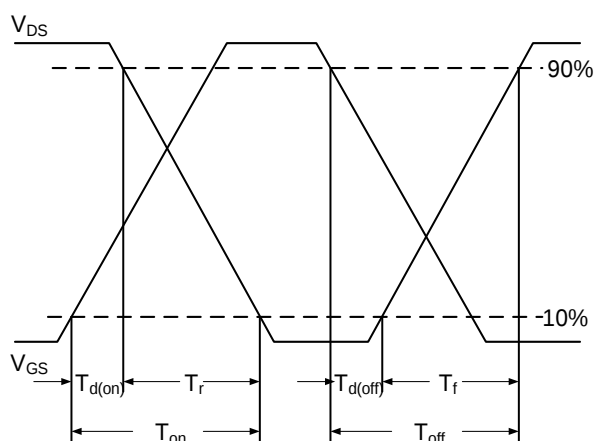


Fig.10 Switching Time Waveform

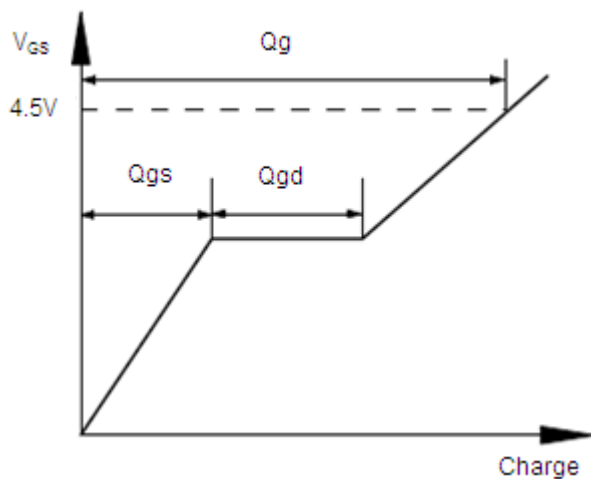
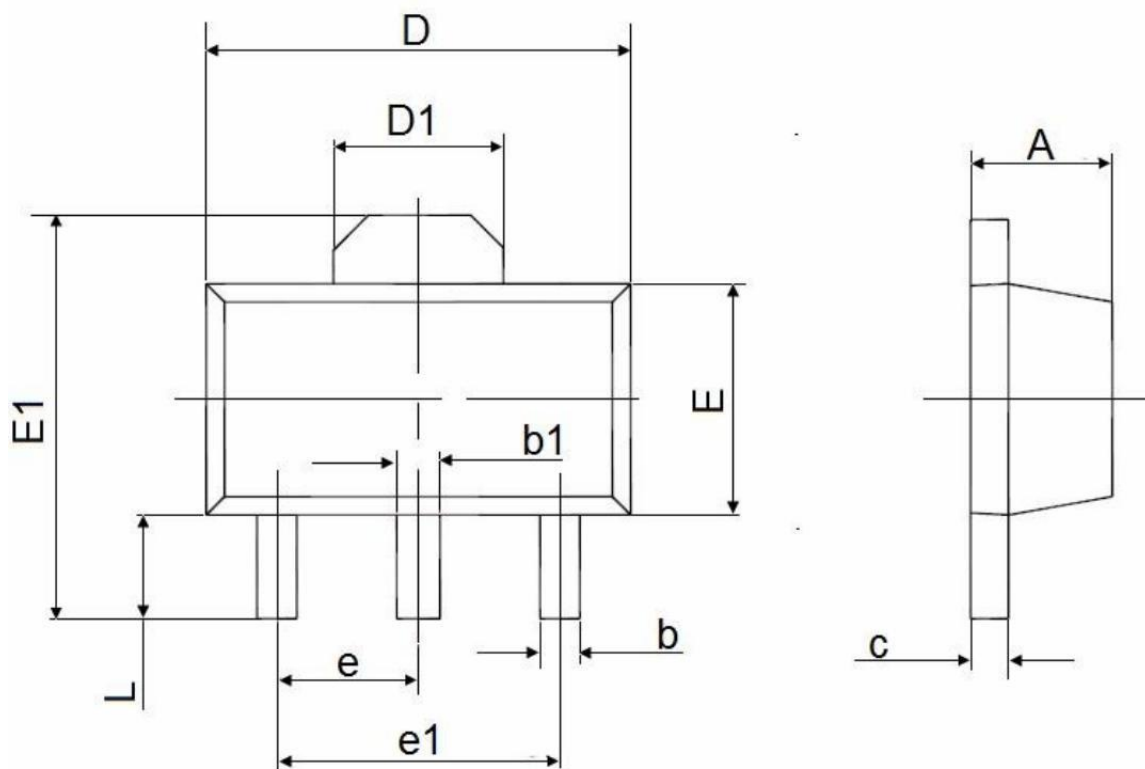


Fig.11 Gate Charge Waveform

Package Mechanical Data-SOT89-3L-YX



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT89-3L		3000